DHG10I600PM

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=

 V_{RRM}

I FAV

trr

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10 A

35 ns

600 V

Sonic Fast Recovery Diode

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Part number

DHG10I600PM



Backside: isolated **E**72873



Features / Advantages:

- Planar passivated chips
- · Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

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Data according to IEC 60747and per semiconductor unless otherwise specified

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Fast Diode					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			600	V	
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			600	V	
I _R	reverse current, drain current	$V_{R} = 600 V$	$T_{VJ} = 25^{\circ}C$			30	μA	
		$V_{R} = 600 V$	$T_{vJ} = 125^{\circ}C$			1.2	mA	
V _F	forward voltage drop	I _F = 10 A	$T_{VJ} = 25^{\circ}C$			2.23	V	
		I _F = 20 A				3.13	V	
		$I_{\rm F} = 10 {\rm A}$	T _{vJ} = 125°C			2.18	V	
		$I_{F} = 20 \text{ A}$				3.29	V	
I FAV	average forward current	$T_c = 25^{\circ}C$	$T_{vJ} = 150 ^{\circ}C$			10	А	
		rectangular d = 0.5						
V _{F0}	threshold voltage		$T_{vJ} = 150^{\circ}C$			1.04	V	
r _F	slope resistance } for power in	oss calculation only				104	mΩ	
R _{thJC}	thermal resistance junction to case	e				4	K/W	
R _{thCH}	thermal resistance case to heatsir	nk			0.50		K/W	
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			30	W	
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_{R} = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			80	А	
C	junction capacitance	$V_{R} = 400 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		6		pF	
I _{RM}	max. reverse recovery current	N N N N N N N N N N N N N N N N N N N	$T_{VJ} = 25 °C$		4		Α	
		$I_{\rm F} = 10 \text{A}; V_{\rm R} = 200 \text{V}$	T _{vJ} = °C		tbd		Α	
t _{rr}	reverse recovery time	I _F = 10 A; V _R = 200 V -di _F /dt = 200 A/μs	$T_{VJ} = 25 ^{\circ}C$		35		ns	
)	T _{vJ} = °C		tbd		ns	

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Package TO-220FP					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					35	Α
T _{vj}	virtual junction temperature				-55		150	°C
T _{op}	operation temperature				-55		125	°C
T _{stg}	storage temperature				-55		150	°C
Weight						2		g
M _D	mounting torque				0.4		0.6	Nm
F _c	mounting force with clip				20		60	Ν
$\mathbf{d}_{Spp/App}$	creepage distance on surface s	triking distance through air	terminal to terminal	3.2	2.7			mm
d _{Spb/Apb}		anning alstande an ough an	terminal to backside	2.5	2.5			mm
V	isolation voltage				2500			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA		2100			V



Part description

D = Diode H = Sonic Fast Recovery Diode

G = extreme fast

10 = Current Rating [A]

I = Single Diode

600 = Reverse Voltage [V] PM = TO-220ACFP (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG10I600PM	DHG10I600PM	Tube	50	503679

Similar Part	Package	Voltage class
DHG10I600PA	TO-220AC (2)	600

Equivalent Circuits for Simulation			* on die level	T _{vj} = 150 °C
)-[Fast Diode		
V _{0 max}	threshold voltage	1.04		V
$\mathbf{R}_{0 \max}$	slope resistance *	101		mΩ

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Outlines TO-220FP





All metal surface are matte pure tin plated except trimmed area.

Dim.	Millim	neters	Inches	
	min	max	min	max
Α	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
b1	1.27	1.47	0.050	0.058
С	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
d1	0	1.10	0	0.043
Е	9.96	10.36	0.392	0.408
е	2.54	BSC	0.100	BSC
Н	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
ØΡ	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



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